

## B772 TRANSISTOR (PNP)

### FEATURES

Power dissipation

$P_{CM}$ : 1.25 W ( $T_{amb}=25^{\circ}C$ )

Collector current

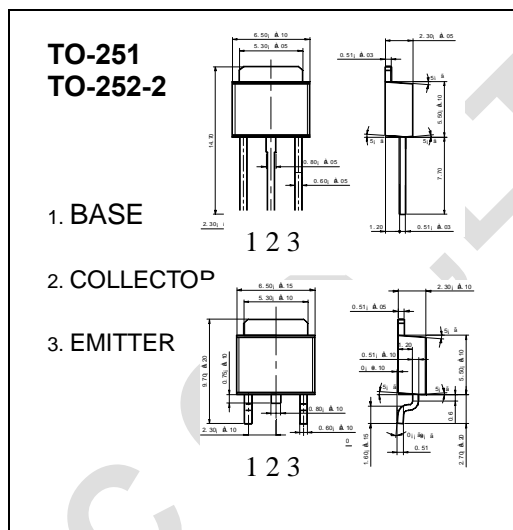
$I_{CM}$ : -3 A

Collector-base voltage

$V_{(BR)CBO}$ : -40 V

Operating and storage junction temperature range

$T_J, T_{stg}$ :  $-55^{\circ}C$  to  $+150^{\circ}C$



### ELECTRICAL CHARACTERISTICS ( $T_{amb}=25^{\circ}C$ unless otherwise specified)

Parameter	Symbol	Test conditions	MIN	TYP	MAX	UNIT
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C = -100\mu A, I_E = 0$	-40			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C = -10mA, I_B = 0$	-30			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E = -100\mu A, I_C = 0$	-6			V
Collector cut-off current	$I_{CBO}$	$V_{CB} = -40V, I_E = 0$			-1	$\mu A$
Collector cut-off current	$I_{CEO}$	$V_{CE} = -30V, I_B = 0$			-10	$\mu A$
Emitter cut-off current	$I_{EBO}$	$V_{EB} = -6V, I_C = 0$			-1	$\mu A$
DC current gain	$h_{FE(1)}$	$V_{CE} = -2V, I_C = -1A$	60		400	
	$h_{FE(2)}$	$V_{CE} = -2V, I_C = -100mA$	32			
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C = -2A, I_B = -0.2A$			-0.5	V
Base-emitter saturation voltage	$V_{BE(sat)}$	$I_C = -2A, I_B = -0.2A$			-1.5	V
Transition frequency	$f_T$	$V_{CE} = -5V, I_C = -0.1A$ $f = 10MHz$	50			MHz

### CLASSIFICATION OF $h_{FE(1)}$

Rank	R	O	Y	GR
Range	60-120	100-200	160-320	200-400